

**In the Specification:**

On page 13, please amend the first full paragraph to read as follows:

The fourth aspect of the invention is method of manufacturing a semiconductor light emitting device by growing nitride III-V compound semiconductor layers forming a light emitting device structure on a nitride III-V compound semiconductor substrate in which a plurality of second regions having a second average ~~dislocation~~defect density higher than a first average ~~dislocation~~defect density align regularly in a first region made of a crystal and having the first average ~~dislocation~~defect density, comprising:

On pages 13-14, please amend the paragraph bridging pages 13 and 14 as follows:

The fifth aspect of the invention is a semiconductor light emitting device manufactured by:  
growing nitride III-V compound semiconductor layers forming a light emitting device structure on a nitride III-V compound semiconductor substrate in which a plurality of second regions having a second average ~~dislocation~~defect density higher than a first average ~~dislocation~~defect density align regularly in a first region made of a crystal and having the first average ~~dislocation~~defect density; and